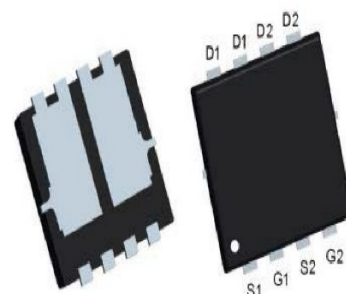
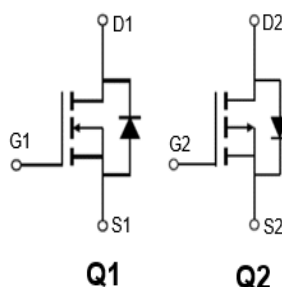


30V/-30V N and P-Channel Enhancement Mode MOSFET

Features

- Q1: $V_{DS}=30V; I_D=30A$
- Q1: $R_{DS(ON)}=10m\Omega$ (TYP.) $V_{GS}=10V, I_D=$
- Q2: $V_{DS}=-30V; I_D=-26A$
- Q2: $R_{DS(ON)}=20m\Omega$ (TYP.) $V_{GS}=-10V, I_D=$
- Reliable and Rugged
- High Current Capability
- Low On-Resistance

PDFN5060



Applications

- Load Switch
- Power management in portable/desktop PCs
- DC/DC conversion

Ordering Information

Device	package	Device Marking	Package Qty.
VSP008C03MD	PDFN5060	*	5000/PCS

Absolute Maximum Ratings ($T_A=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Value(Q1)	Value(Q2)	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	30	-30	V
Gate-Source Voltage ($V_{GS}=0V$, static)	V_{GS}	± 20	± 20	V
Continuous Drain Current ($T_C=25^{\circ}C$)	I_D	30	-26	A
Continuous Drain Current ($T_C=100^{\circ}C$)		20	-18	A
Pulesd Drain Current	I_{DM}	110	-100	A
Avalanche Current	I_{AS}	12	-16	A
Single Pulsed Avalanche Energy	E_{AS}	20	18	mJ
Maximum Power Dissipation ($T_C=25^{\circ}C$)	P_D	4	4.5	W
Maximum Power Dissipation ($T_C=100^{\circ}C$)		2	2.5	W
Operating, Storage Temperature Range	T_J, T_{STG}	-55~150	-55~150	$^{\circ}C$

Q1:Electrical Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate -Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.1	1.5	1.9	V
Drain-Source On-stage Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=1A$	-	7.5	10	m Ω
		$V_{GS}=4.5V, I_D=1A$	-	11	18	

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	14	-	$^{\circ}\text{C}/\text{W}$
Thermal Resistance,Junction-to-Ambient	$R_{\theta JA}$	63	-	$^{\circ}\text{C}/\text{W}$

Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$V_{DS}=20\text{V}$	-	935	-	pF
Output capacitance	C_{oss}	$V_{GS}=0\text{V}$	-	128	-	
Reverse transfer capacitance	C_{rss}	$f=1\text{MHz}$	-	105	-	
Gate Resistance	R_g	$f=1\text{MHz}$	-	3.9	-	Ω
Total Gate Charge	Q_g	$V_{DS}=20\text{V}$	-	10	-	nC
Gate Source Charge	Q_{gs}	$V_{GS}=10\text{V}$	-	3.2	-	
Gate Drain Charge	Q_{gd}	$I_D=6\text{A}$	-	2	-	
Turn-on delay Time	$t_{d(on)}$	$V_{GS}=10\text{V}$	-	5	-	ns
Rise time	t_r	$V_{DS}=20\text{V}$	-	3	-	
Turn-off delay Time	$t_{d(off)}$	$R_L=3.2\Omega$	-	16	-	
Fall time	t_f	$R_G=3\Omega$	-	6	-	
Body Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}, I_{SD}=1\text{A}$	-	0.7	1	V
Reverse Recovery Time	t_{rr}	$V_{GS}=0\text{V}, I_{SD}=6\text{A}$	-	10	-	ns
Reverse Recovery Charge	Q_{rr}	$d_i/d_t=500\text{A}/\mu\text{s}$	-	13	-	nC

Q1:Electrical Characteristics Diagrames

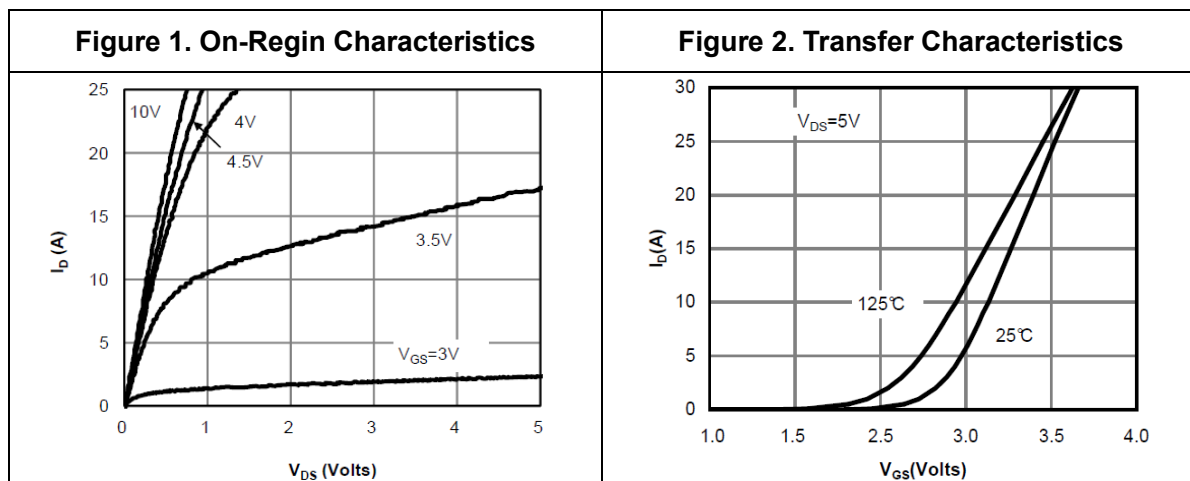
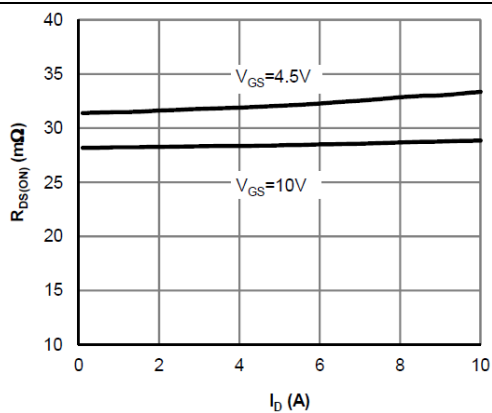
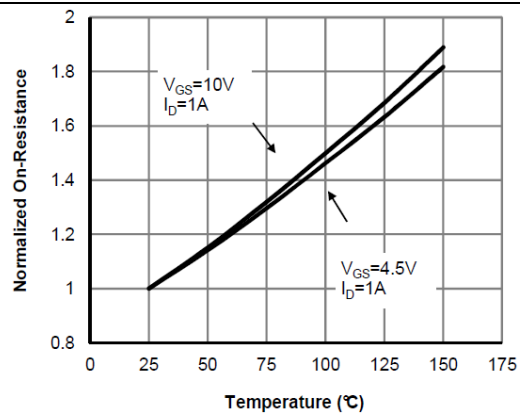
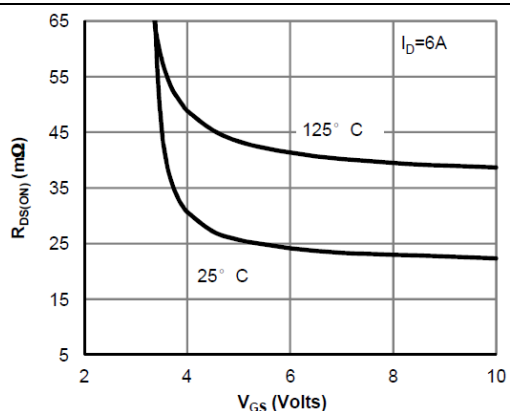
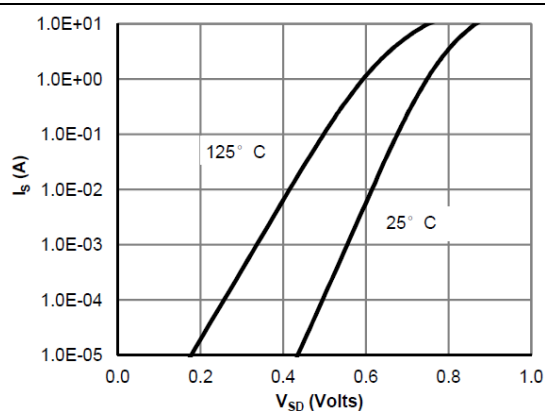
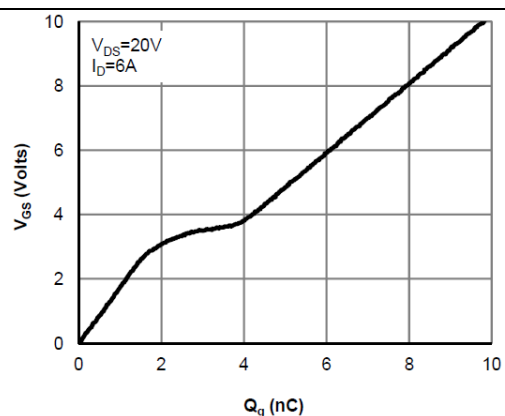
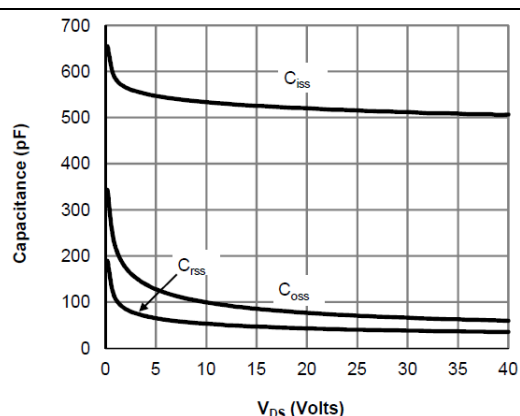
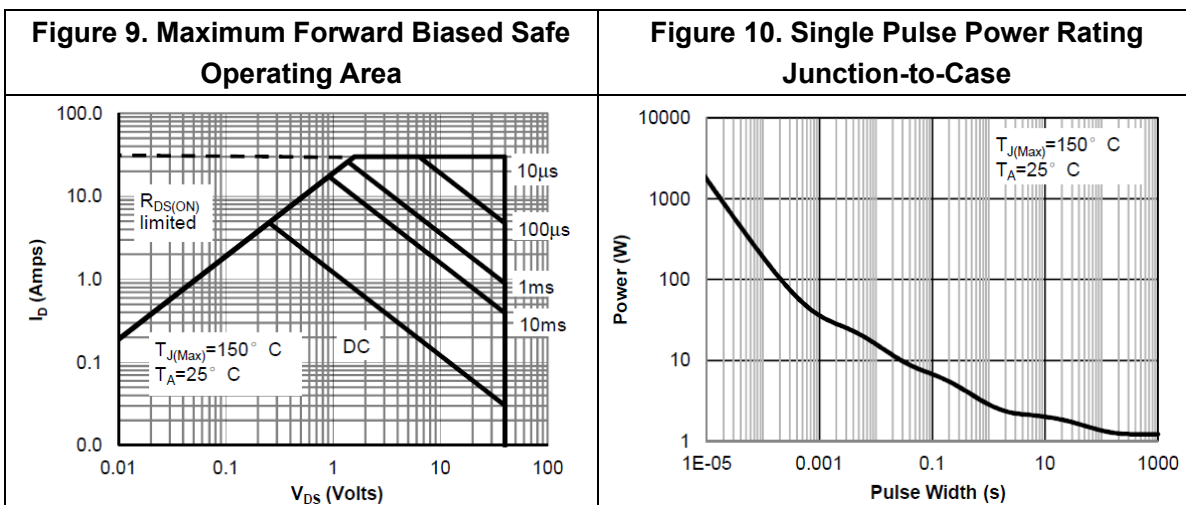


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

Figure 4. On-Resistance vs. Junction Temperature

Figure 5. On-Resistance vs. Gate-Source Voltage

Figure 6. Body-Diode Characteristics

Figure 7. Gate-Charge Characteristics

Figure 8. Capacitance Characteristics




Q2:Electrical Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	μA
Gate -Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.1	-1.5	-1.9	V
Drain-Source On-stage Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-1A$	-	16	20	m Ω
		$V_{GS}=-4.5V, I_D=-1A$	-	26	32	

Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$V_{DS}=-20V$ $V_{GS}=0V$ $f=1MHz$	-	1220	-	pF
Output capacitance	C_{oss}		-	156	-	
Reverse transfer capacitance	C_{rss}		-	87	-	
Gate Resistance	R_g	$f=1MHz$	-	8.9	-	Ω
Total Gate Charge	Q_g	$V_{DS}=-20V$ $V_{GS}=-10V$ $I_D=-5A$	-	17	-	nC
Gate Source Charge	Q_{gs}		-	3.5	-	
Gate Drain Charge	Q_{gd}		-	3	-	
Turn-on delay Time	$t_{d(on)}$	$V_{GS}=-10V$ $V_{DS}=-20V$ $R_L=4\Omega$ $R_G=3\Omega$	-	6.5	-	ns
Rise time	t_r		-	7.8	-	
Turn-off delay Time	$t_{d(off)}$		-	45	-	
Fall time	t_f		-	40	-	
Body Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD}=-1A$	-	-0.7	-1	V
Reverse Recovery Time	t_{rr}	$V_{GS}=0V, I_{SD}=-5A$ $d_i/d_t=500A/\mu s$	-	22	-	ns
Reverse Recovery Charge	Q_{rr}		-	15	-	nC

Q2:Electrical Characteristics Diagrames

Figure 1. On-Regin Characteristics

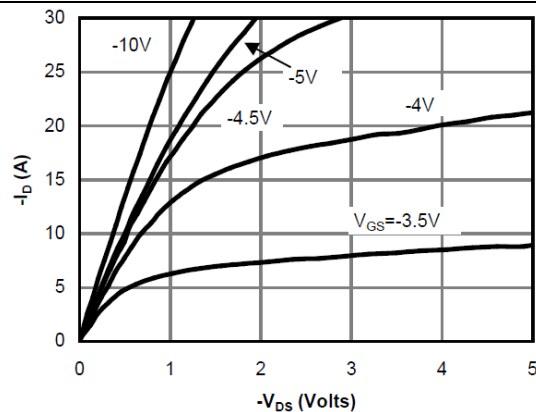


Figure 2. Transfer Characteristics

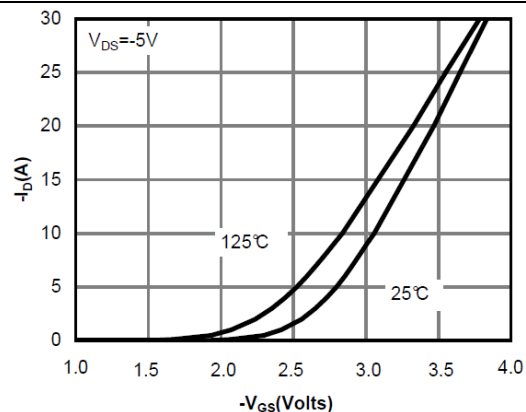


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

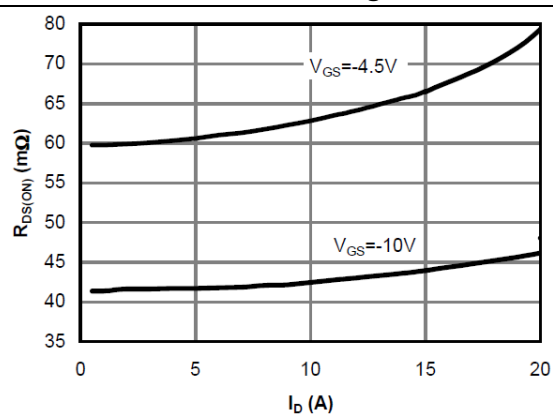


Figure 4. On-Resistance vs. Junction Temperature

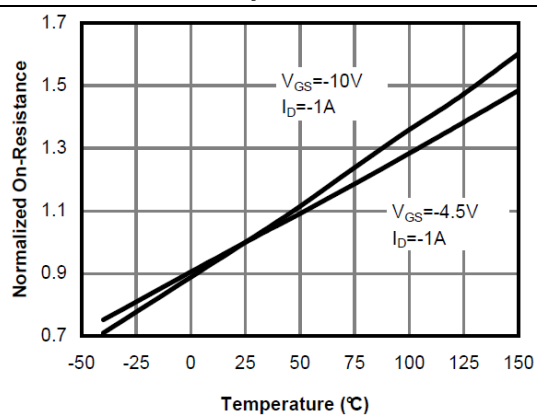


Figure 5. On-Resistance vs. Gate-Source Voltage

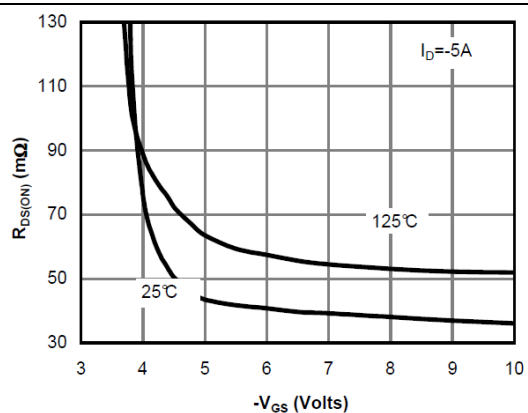


Figure 6. Body-Diode Characteristics

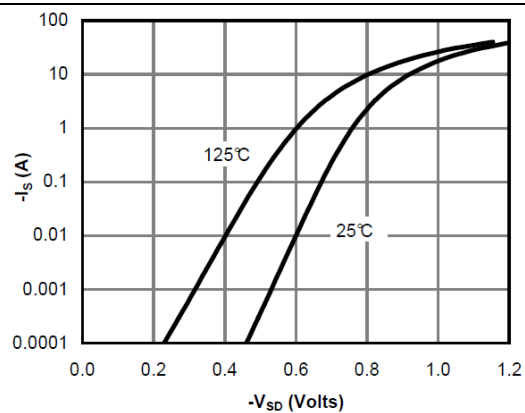
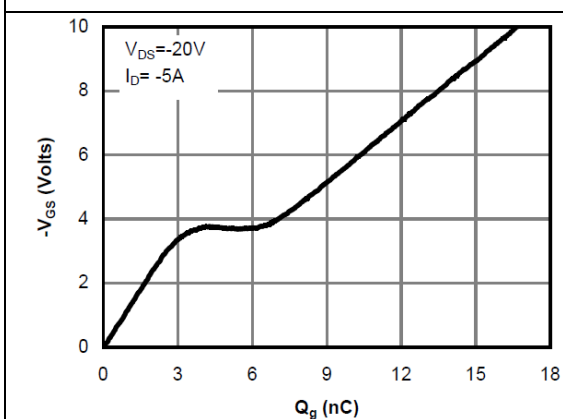
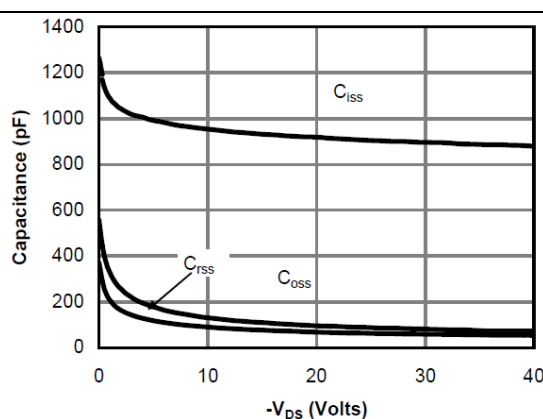
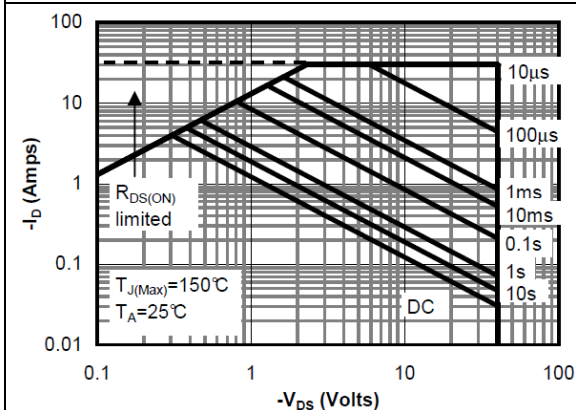
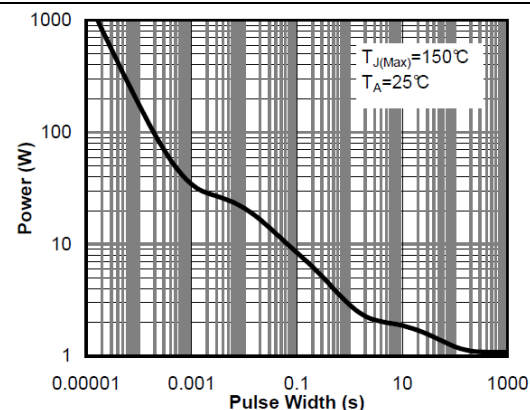
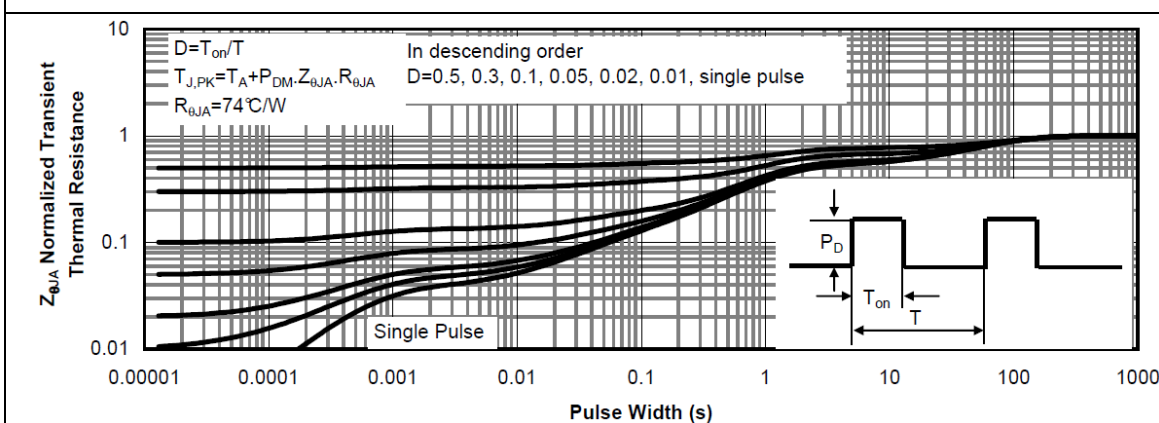


Figure 7. Gate-Charge Characteristics

Figure 8. Capacitance Characteristics

Figure 9. Maximum Forward Biased Safe Operating Area

Figure 10. Single Pulse Power Rating Junction-to-Case

Figure 11. Normalized Maximum Transient Thermal Impedance


< Copyright >

All the Patent, Copyright and IP contained in this document belong to HAMOS, shall not be reproduced, copied, or used in other ways without permission.